

### 40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

## **Product Summary**

BVDSS	R <sub>DS(ON)</sub> Max	Qg Typ	I <sub>D</sub> T <sub>C</sub> = +25°C
40V	2.7mΩ @ V <sub>GS</sub> = 10V	68.6nC	100A

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

PowerDI5060-8/SWP (Type UX)

Engine management systems

Top View

Ordering Information (Note 4)

- Body control electronics
- DC-DC converters

### **Features**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> Minimizes Power Losses
- Low Q<sub>g</sub> Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH4004SPSWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

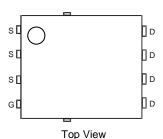
#### **Mechanical Data**

- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (§)
- Weight: 0.097 grams (Approximate)



Pin1





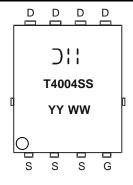
Pin Configuration

Part Number	Packago	Packing		
Part Number	Fackage	Qty.	Carrier	
DMTH4004SPSWQ-13	PowerDI5060-8/SWP (Type UX)	2,500	Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



**Bottom View** 

⊃¦¦ = Manufacturer's Marking T4004SS = Product Type Marking Code YYWW = Date Code Marking YY or YY = Year (ex: 23 = 2023) WW = Week (01 to 53)



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	40	V	
Gate-Source Voltage		$V_{GSS}$	±20	V
Continuous Drain Current (Note 5)	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	lο	31 26	А
To			100	
Continuous Drain Current (Note 6)	T <sub>C</sub> = +100°C (Note 8)	lD	100	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	350	Α	
Maximum Continuous Body Diode Forward Current (Note 5)	Is	100	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	Isм	350	Α	
Avalanche Current, L=0.2mH		I <sub>AS</sub>	45	Α
Avalanche Energy, L=0.2mH	Eas	200	mJ	

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5) $T_A = +25^{\circ}C$		P <sub>D</sub>	3.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Reja	41	°C/W	
Total Power Dissipation (Note 6)	PD	167	W	
Thermal Resistance, Junction to Case (Note 6)	R <sub>0</sub> JC	0.9	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +175	°C	

### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

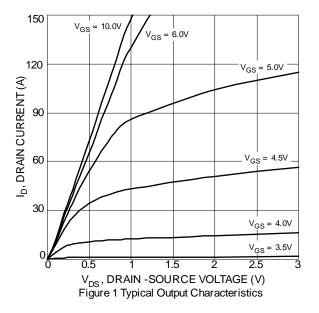
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40		_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	l	1	1	μΑ	V <sub>DS</sub> = 32V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	Igss	-	_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	_	4	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		2.3	2.7	mΩ	$V_{GS} = 10V, I_D = 90A$	
Diode Forward Voltage	VsD	l	0.9	1.2	V	V <sub>G</sub> S = 0V, I <sub>S</sub> = 20A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		4,305	_		V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	1,441	_	pF		
Reverse Transfer Capacitance	Crss	l	102	_			
Gate Resistance	Rg	-	0.77	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	_	68.6	_		V <sub>DD</sub> = 20V, I <sub>D</sub> = 90A, V <sub>GS</sub> = 10V	
Gate-Source Charge	Qgs	_	16.8	_	nC		
Gate-Drain Charge	Qgd	_	14.2	_			
Turn-On Delay Time	tD(ON)	_	9.5	_			
Turn-On Rise Time	t <sub>R</sub>	_	6.7	_		$V_{DD} = 20V$ , $V_{GS} = 10V$ , $I_{D} = 90A$ , $R_{G} = 3.5\Omega$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	26.4	_	ns		
Turn-Off Fall Time	tF	_	8.1	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	52.4	_	ns	I_ FOA d:/dt 100A/up	
Body Diode Reverse Recovery Charge	Qrr		78.2	_	nC		

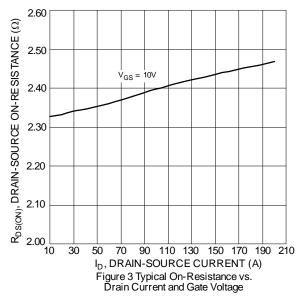
Notes:

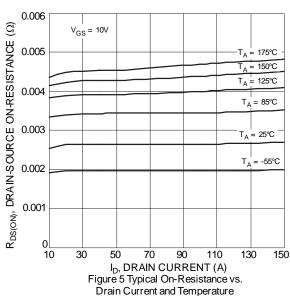
- 5. Device mounted with exposed drain pad on 25mm by 25mm 2oz copper on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions 5. Device mounted with exposed train pad on 25mm by 25mm 252 copper 51 a 51 whilst operating in a steady state.
  6. Thermal resistance from junction to soldering point (on the exposed drain pad).
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to production testing

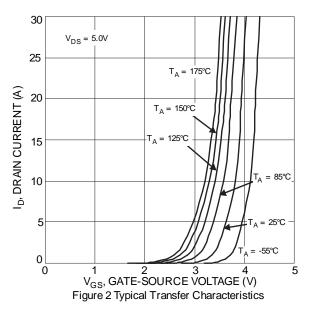


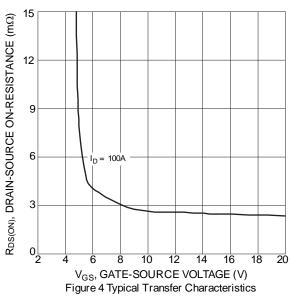












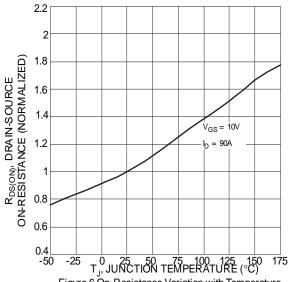
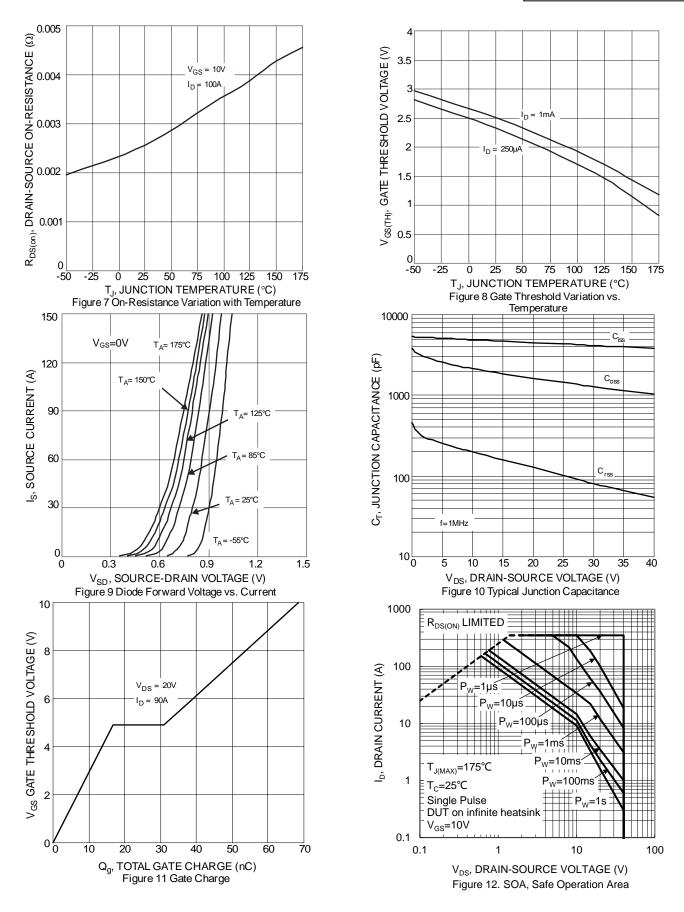


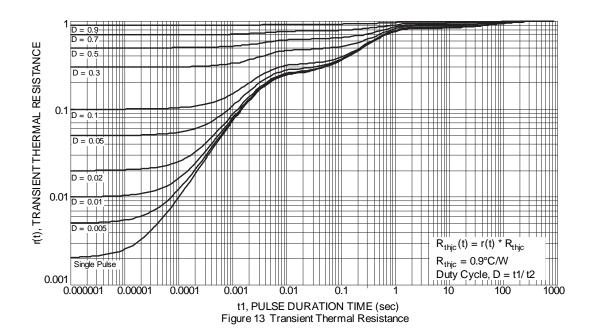
Figure 6 On-Resistance Variation with Temperature









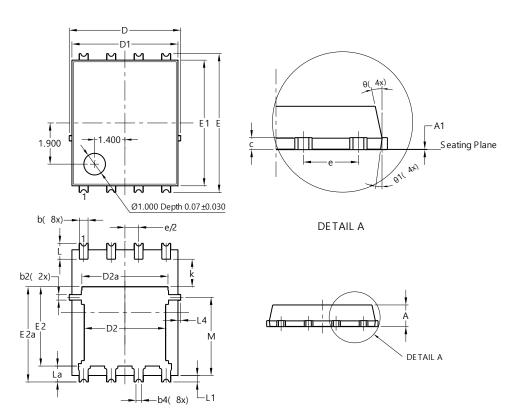




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8/SWP (Type UX)

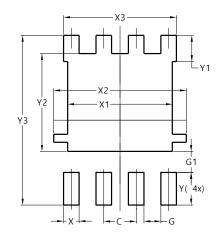


PowerDI5060-8/SWP (Type UX)					
Dim	Min	Тур			
Α	0.90	1.10	1.00		
A1	0	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4	(	).25REF			
С	0.230	0.330	0.277		
D	5.15 BSC				
D1	4.70	5.10	4.90		
D2	3.56	3.96	3.76		
D2a	3.78 4.18 3.98				
Е	6.40 BSC				
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е	1	.27BSC	)		
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L1a	0.050REF				
L4	0.025	0.225	0.125		
M	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)	
С	1.270	
G	0.660	
G1	0.820	
X	0.610	
X1	4.100	
X2	5.190	
Х3	4.420	
Y	1.270	
Y1	1.020	
Y2	3.810	
Y3	6.610	



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